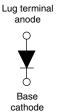
Vishay Semiconductors

High Performance Schottky Rectifier, 120 A



www.vishay.com

HALF-PAK (D-67)



| PRIMARY CHARACTERISTICS | | | |
|--------------------------|-----------------|--|--|
| I _{F(AV)} 120 A | | | |
| V _R | 30 V | | |
| Package | HALF-PAK (D-67) | | |
| Circuit configuration | Single | | |

FEATURES

- 150 °C T_J operation
- Low forward voltage drop
- High frequency operation
- · Guard ring for enhanced ruggedness and long term reliability
- Designed and qualified for industrial level
- UL approved file E222165
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION

The VS-122NQ.. high current Schottky rectifier module series has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 175 °C junction temperature. Typical applications are in high current switching power supplies, plating power supplies, UPS systems, converters, freewheeling diodes, welding, and reverse battery protection.

| MAJOR RATINGS AND CHARACTERISTICS | | | | | |
|-----------------------------------|---|------------------------|----|--|--|
| SYMBOL | CHARACTERISTICS | CHARACTERISTICS VALUES | | | |
| I _{F(AV)} | Rectangular waveform | 120 | A | | |
| V _{RRM} | | 30 | V | | |
| I _{FSM} | t _p = 5 μs sine | 18 000 | A | | |
| V _F | 120 A _{pk} , T _J = 125 °C | 0.47 | V | | |
| TJ | Range | -55 to +150 | °C | | |

| VOLTAGE RATINGS | | | | |
|--------------------------------------|------------------|----------------|-------|--|
| PARAMETER | SYMBOL | VS-122NQ030PbF | UNITS | |
| Maximum DC reverse voltage | V _R | 30 | V | |
| Maximum working peak reverse voltage | V _{RWM} | 30 | v | |

| ABSOLUTE MAXIMUM RATINGS | | | | | |
|--|--------------------|---|---|--------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | VALUES | UNITS |
| Maximum average forward current See fig. 5 | I _{F(AV)} | 50 % duty cycle at T_C = 115 °C, rectangular waveform | | 120 | А |
| Maximum peak one cycle non-repetitive surge current | | 5 µs sine or 3 µs rect. pulse | Following any rated load condition and with rated | 18 000 | A |
| See fig. 7 | I _{FSM} | 10 ms sine or 6 ms rect. pulse | V _{RRM} applied | 2000 | |
| Non-repetitive avalanche energy | E _{AS} | T _J = 25 °C, I _{AS} = 11 A, L = 1 mH | | 54 | mJ |
| Repetitive avalanche current | I _{AR} | Current decaying linearly to zero in 1 μ s Frequency limited by T _J maximum V _A = 1.5 x V _R typical | | 12 | А |

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| ELECTRICAL SPECIFICATIONS | | | | | |
|--|--------------------------------|---|---------------------------------|--------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | VALUES | UNITS |
| | V _{FM} ⁽¹⁾ | 120 A | T.I = 25 °C | 0.57 | V |
| Maximum forward voltage drop per leg | | 240 A | 1j=25 0 | 0.75 | |
| See fig. 1 | VFM V | 120 A | T.I = 125 °C | 0.47 | |
| | | 240 A | 1j = 123 0 | 0.67 | |
| Maximum reverse leakage current per leg | I _{RM} ⁽¹⁾ | T _J = 25 °C | $V_{\rm B}$ = Rated $V_{\rm B}$ | 10 | mA |
| See fig. 2 | | | VR - naleu VR | 560 | ША |
| Maximum junction capacitance | CT | $V_R = 5 V_{DC}$ (test signal range 100 kHz to 1 MHz) 25 °C 7 | | 7400 | pF |
| Typical series inductance | L _S | From top of terminal hole to mounting plane 7. | | 7.0 | nH |
| Maximum voltage rate of change | dV/dt | Rated V _R 10 000 | | V/µs | |

Note

 $^{(1)}\,$ Pulse width < 300 $\mu s,$ duty cycle < 2 $\,\%$

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | |
|--|--|-----------------------------------|--------------------------------------|------------|------------|--|
| PARAMETER | | SYMBOL | TEST CONDITIONS | VALUES | UNITS | |
| Maximum junction and storage te | mperature range | T _J , T _{Stg} | | -55 to 150 | °C | |
| Maximum thermal resistance, junction to case | | R _{thJC} | DC operation See fig. 4 | 0.38 | °C/W | |
| Typical thermal resistance, case t | pical thermal resistance, case to heatsink R | | Mounting surface, smooth and greased | 0.05 | | |
| Approximate weight | | | | 30 | g | |
| | | | | 1.06 | oz. | |
| | minimum | | | 3 (26.5) | | |
| Mounting torque maximum | | | Non-lubric stand days and | 4 (35.4) | N ⋅ m | |
| Terminal torque | minimum | | Non-lubricated threads | 3.4 (30) | (lbf · in) | |
| | maximum | | | 5 (44.2) | | |
| Case style | se style | | | HALF-PA | K module | |

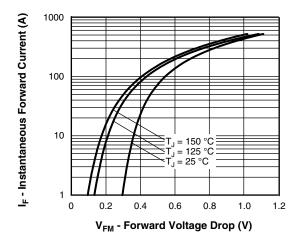


Fig. 1 - Maximum Forward Voltage Drop Characteristics

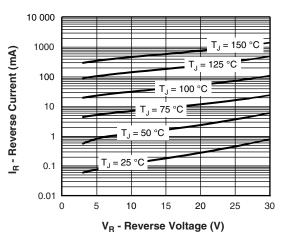


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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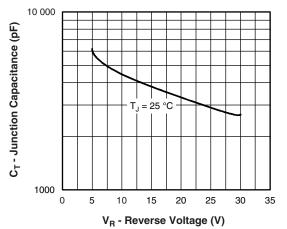


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

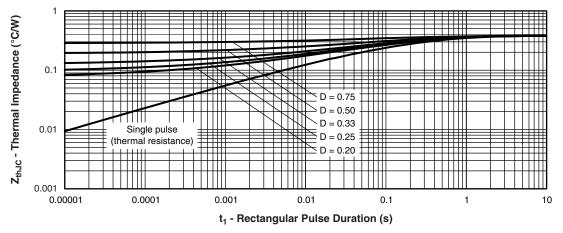
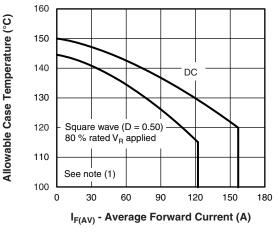
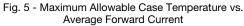


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics





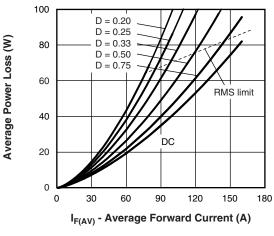


Fig. 6 - Forward Power Loss Characteristics

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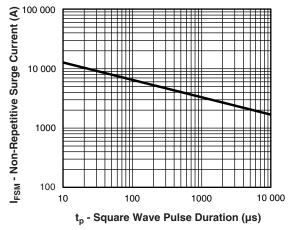


Fig. 7 - Maximum Non-Repetitive Surge Current

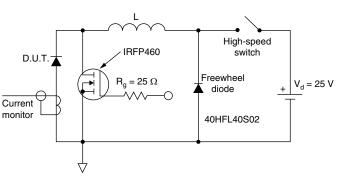
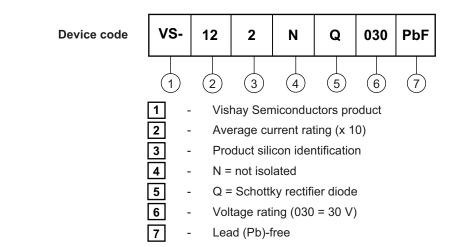


Fig. 8 - Unclamped Inductive Test Circuit

Note

 Pd_{REV} = inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = rated V_R

ORDERING INFORMATION TABLE



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 $^{^{(1)} \}mbox{ Formula used: } T_C = T_J - (Pd + Pd_{REV}) \ x \ R_{thJC}; \\ Pd = \mbox{ Forward power loss } = I_{F(AV)} \ x \ V_{FM} \ at \ (I_{F(AV)}/D) \ (see \ fig. \ 6);$

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17.5 (0.69) 16.5 (0.65)



DIMENSIONS in millimeters (inches)

SHAY





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